

isc N-Channel MOSFET Transistor

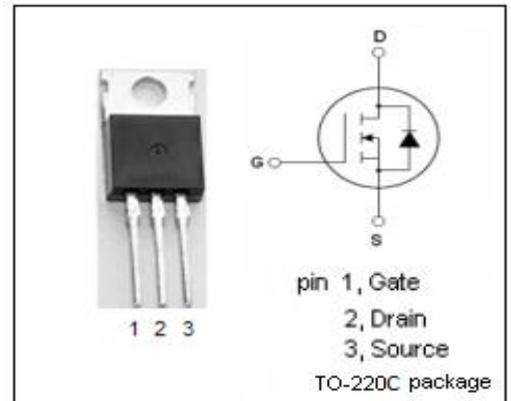
33N10

FEATURES

- Static drain-source on-resistance:
 $R_{DS(on)} \leq 60m\Omega$
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

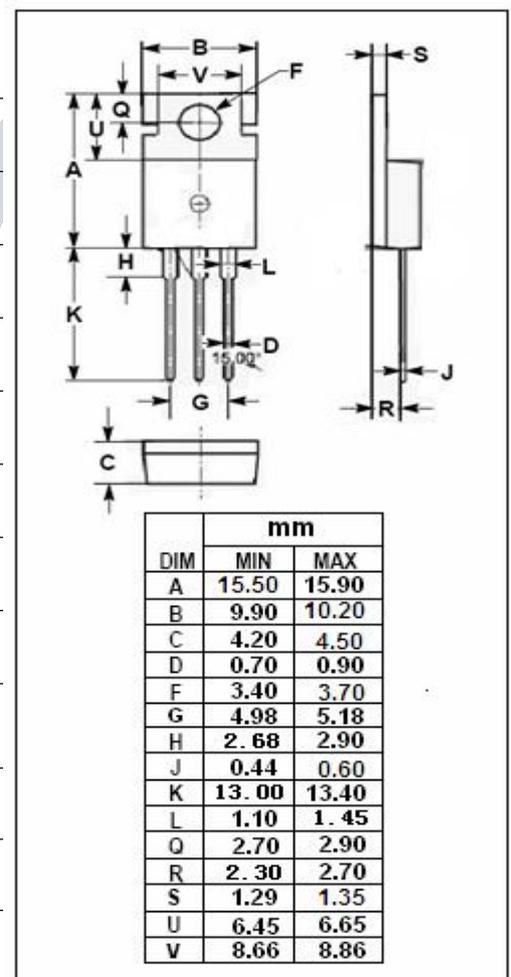
DESCRIPTION

- Switching power supplies, converters, AC and DC motor controls



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|--------------------------------------|----------|------------|
| V_{DSS} | Drain-Source Voltage | 100 | V |
| V_{GS} | Gate-Source Voltage | ± 30 | V |
| I_D | Drain Current-Continuous | 33 | A |
| I_{DM} | Drain Current-Single Pulsed | 132 | A |
| P_D | Total Dissipation @ $T_c=25^\circ C$ | 150 | W |
| T_j | Max. Operating Junction Temperature | 150 | $^\circ C$ |
| T_{stg} | Storage Temperature | -55~150 | $^\circ C$ |



THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|----------------|---------------------------------------|------|--------------|
| $R_{th(ch-c)}$ | Channel-to-case thermal resistance | 1.0 | $^\circ C/W$ |
| $R_{th(ch-a)}$ | Channel-to-ambient thermal resistance | 62.5 | $^\circ C/W$ |

isc N-Channel MOSFET Transistor**33N10****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------|--------------------------------|--|-----|-----|-----------|------------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS}=0V; I_D=250\ \mu\text{A}$ | 100 | | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}; I_D=250\ \mu\text{A}$ | 2 | | 4 | V |
| $R_{DS(on)}$ | Drain-Source On-Resistance | $V_{GS}=10V; I_D=17A$ | | | 60 | $\text{m}\Omega$ |
| I_{GSS} | Gate-Source Leakage Current | $V_{GS}=\pm 20V; V_{DS}=0V$ | | | ± 100 | nA |
| I_{DSS} | Drain-Source Leakage Current | $V_{DS}=100V; V_{GS}=0V$ | | | 250 | μA |
| V_{SD} | Diode forward voltage | $I_S=33A; V_{GS}=0V$ | | | 2 | V |
| C_{iss} | Input Capacitance | | | | 2000 | pF |
| C_{rss} | Reverse Transfer capacitance | $V_{DS}=25V; V_{GS}=0V; f_T=1\text{MHz}$ | | | 100 | |
| C_{oss} | Output Capacitance | | | | 600 | |

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